A PA-CVD PROCESS FOR DEPOSITION OF A SOLID METAL-CONTAINING FILM ONTO A SUBSTRATE CONTAINING AT LEAST 50 % of Fe or W.C

PA-CVD PROCESS FOR DEPOSITION OF A SOUD METAL-CONTAINING FILM ONTO A SUBSTRATE CONTAINING AT 500 % of Fe or VXC

Patent Number:

WO9618756

Publication date:

1996-06-20

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Requested Patent:

WO9618756

Application

Number:

WO1995DK00505 19951215

Priority Number(s): DK19940001436 19941216

IPC Classification: C23C16/08; C23C16/30; C23C16/50

EC Classification:

C23C16/08, C23C16/32, C23C16/34

EC Classification:

C23C16/08; C23C16/32; C23C16/34

Equivalents:

Abstract

A new plasma assisted chemical vapour deposition (PA-CVD) process for deposition of a solid metal-containing film onto the surface of a substrate containing at least 50 % of Fe or WC (such as hard metal or steel), by which the metallic component of the metal-containing film is introduced into the system as a metal halide, is disclosed. The new process involves shifting the process gas composition between a high and a low metal halide level, whereby the adhesion of the deposited film to the substrate is improved.